

# Silicon Hot -Carrier Diodes

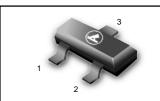
These devices are designed primarily for high–efficiency UHF and VHF detector applications. They are readily adaptable to many other fast switching RF and digital applications. They are supplied in an inexpensive plastic package for low–cost,high–volume consumer and industrial/commercial requirements. They are also available in a Surface Mount package.

- Extremely Low Minority Carrier Lifetime 15 ps (Typ)
- Very Low Capacitance 1.0 pF @ V R = 20 V
- High Reverse Voltage to 70 Volts
- Low Reverse Leakage 200 nA (Max)



# MBD701 MMBD701LT1

70 VOLTS
HIGH-VOLTAGE
SILICON HOT-CARRIER
DETECTOR AND SWITCHING
DIODES



CASE 318-08, STYLE8 SOT- 23 (TO-236AB)

#### MAXIMUM RATINGS (T J = 125°C unless otherwise noted)

		MBD701	MMBD701LT1			
Rating	Symbol	Va	Unit			
Reverse Voltage	$V_R$	7	Volts			
Forward Power Dissipation	P <sub>F</sub>					
@ T <sub>A</sub> = 25°C		280	200	mW		
Derate above 25°C		2.8	2.0	mW/°C		
Operating Junction	ΤJ			℃		
Temperature Range		−55 to +125				
Storage Temperature Range	T stg	–55 t	S			

#### **DEVICE MARKING**

MMBD701LT1 = 5H

### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	typ	Max	Unit
Reverse Breakdown Voltage (I <sub>R</sub> = 10μAdc)	$V_{(BR)R}$	70	_	_	Volts
Total Capacitance (V <sub>R</sub> = 20 V, f = 1.0 MHz) Figure 1	Ст	_	0.5	1.0	pF
Reverse Leakage (V <sub>R</sub> = 35 V) Figure 3	I <sub>R</sub>	_	9.0	200	nAdc
Forward Voltage (I <sub>F</sub> = 1.0 mAdc) Figure 4	V <sub>F</sub>	_	0.42	0.5	Vdc
Forward Voltage (I <sub>F</sub> = 10 mAdc) Figure 4	V <sub>F</sub>	_	0.7	1.0	Vdc

NOTE: MMBD701LT1 is also available in bulk packaging. Use MMBD701L as the device title to order this device in bulk.



## MBD701 MMBD701LT1

#### TYPICAL ELECTRICAL CHARACTERISTICS

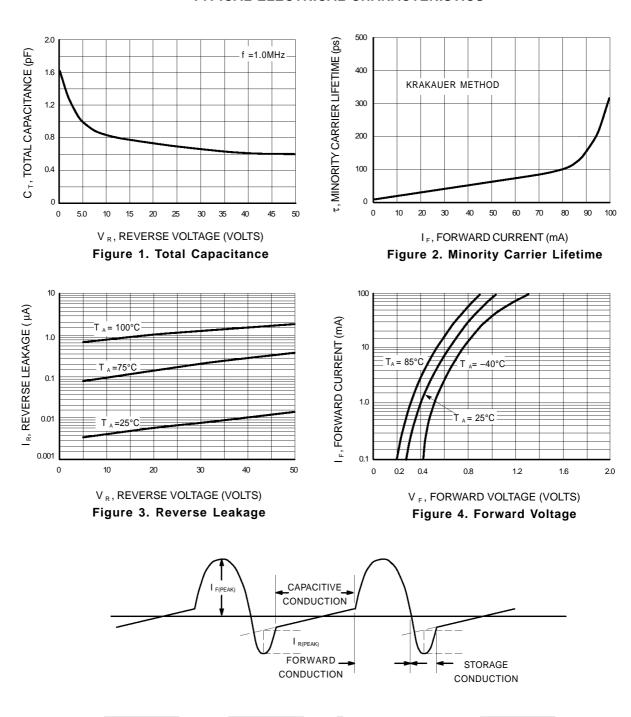


Figure 5. Krakauer Method of Measuring Lifetime

PADS

BALLAST

NETWORK

(PADS)

SINUSOIDAL

**GENERATOR** 

SAMPLING

OSCILLOSCOPE

(50 Ω INPUT)